## MN74HC00/MN74HC00S

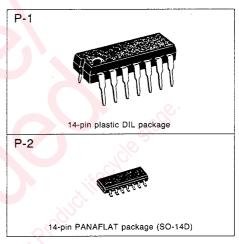
### Quad 2-Input NAND Gates

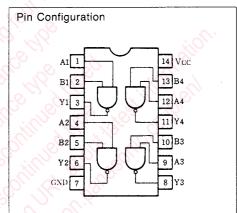
#### ■ Outline

The MN74HC00/MN74HC00S is a 2-input positive logic NAND gate having four built-in circuits in one chip. Owing to the silicon gate CMOS process, this NAND gate has realized low power consumption and high noise immunity equivalent to those of a sandard CMOS and the operation speed as high as of an LS TTL. The buffer added to the gate output improves the input/ output transfer characteristic and minimizes the propagation delay time fluctuation caused by the load capacity increase. The MN74HC00/MN74HC00S can directly drive ten LS TTL inputs. To protect the input and output against electrostatic breakdown, a resistor and a diode are used for the Vcc and the GND. The pin configuration and the function are the same as those of the standard 54LS/74LS logic family.

#### ■ Logic Diagram (1 Gate)







#### ■ Absolute Maximum Ratings

Item			Symbol	Rating	Unit
Supply voltage			V <sub>cc</sub>	-0.5~+7.0	V
Input output voltage			V <sub>I</sub> , V <sub>O</sub>	-0.5~V <sub>cc</sub> +0.5	V
Input protective diode current			$I_{IK}$	±20	mA
Output parasitic diode current			Iok	±20	mA
Output current			$I_{O}$	±25	mA
Supply current			I <sub>CC</sub> , I <sub>GND</sub>	±50	mA
Storage temperature			$T_{\text{stg}}$	-65~+150	°C
Power dissipation	MN74HC00	$Ta = -40 \sim +60^{\circ}C$	D	400	W
		$Ta = +60 \sim +85^{\circ}C$	$P_D$	Decrease to 200mW at the rate of 8mW/°C	mW
	MN74HC00S	$Ta = -40 \sim +60 ^{\circ}C$	D	275	
	WIIV/411C005	$Ta = +60 \sim +85^{\circ}C$	$P_D$	Decrease to 200mW at the rate of 3.8mW/°C	mW

■ Recommended Operating Conditions

Item	Symbol	V <sub>cc</sub> (V)	Rating	Unit	
Operating power supply voltage	V <sub>cc</sub>		1.4~6.0	V	
Input output voltage	V <sub>I</sub> , V <sub>O</sub>		0~V <sub>cc</sub>	V	
Operating temperature	T <sub>A</sub>		-40~+85	°C	
		2.0	0~1000	ns	
Input rise, fall time	t <sub>r</sub> , t <sub>f</sub>	4.5	0~500	ns	
	Waling on the state of the stat	6.0	0~400	ns	

■ DC Characteristics (GND=0V)

	Symbol	V <sub>cc</sub> (V)	Test Condition			Temperature					
Item			VI	T	T		Ta=25°C			Ta=-40~+85°C	
				$I_0$	Unit	min.	typ.	max.	min.	max.	
		2.0				1.5			1.5		
Input voltage high level	$V_{IH}$	4.5				3.15			3.15	1	V
		6.0				4.2		_C	4.2		
		2.0						0.3		0.3	
Input voltage low level	$V_{IL}$	4.5						0.9		0.9	V
		6.0						1.2		1.2	
		2.0		-20.0	μΑ	1.9	2.0		1.9		
		4.5	$V_{IH}$	-20.0	$\mu$ A	4.4	4.5		4.4		
Output voltage high level	Voh	6.0	or	-20.0	μΑ	5.9	6.0		5.9		V
		4.5	V <sub>IL</sub>	-4.0	mA	3.92	C		3.84		
		6.0		-5.2	mA	5.48	K		5.34	Ý	
		2.0		20.0	μΑ	-C	0.0	0.1		0.1	ο,
		4.5		20.0	μΑ		0.0	0.1		0.1	
Output voltage low level	Vol	6.0	VIH	20.0	$\mu$ A		0.0	0.1		0.1	V
		4.5		.4.0	mA	~CO	00	0.26	6	0.33	
		6.0		5.2	mA		200	0.26	(8)	0.33	
Input leakage current	$I_{I}$	6.0	V <sub>1</sub> =V <sub>cc</sub> or GND			4/1/	7	±0.1	P	±1.0	μΑ
Static supply current	$I_{cc}$	6.0	$V_1 = V_{CC}$ or GND, $I_0 = 0$		<sup>C</sup> Ö.	6	2.0		20.0	μΑ	

## ■ AC Characteristics (GND=0V, Input transition time≤6ns, C<sub>L</sub>=50pF)

	Symbol	V <sub>cc</sub> (V)		$\mathcal{O}_{\mathcal{O}}}}}}}}}}$					
Item			Test Condition	Ta=25°C			$Ta = -40 \sim +85^{\circ}C$		Unit
			6.	min.	typ.	max.	min.	max.	
	5	2.0		21/2	25	75		95	
Output rise time	t <sub>TLH</sub>	4.5	103	1,5	8	15		19	ns
		6.0		$\eta_{B}$ .	7	13		16	
1311	t <sub>THL</sub>	2.0	113 114	7	20	75		95	
Output fall time		4.5	co "0; j,		7	15		19	ns
		6.0	JOS VILLA		6	13		16	
		2.0			25	75		95	
Propagation time (L→H)	t <sub>PLH</sub>	4.5			8	15		19	ns
•		6.0			7	13		16	
		2.0			25	75		95	
Propagation time $(H\rightarrow L)$	t <sub>PHL</sub>	4.5			8	15		19	ns
		6.0			7	13		16	

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